Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (currently amended) A semiconductor component comprising a semiconductor chip made of a doped silicon substrate, which chip is doped into a semiconductor device and structured, and comprises an inner connection metallization in a contact window, and said inner connection metallization of said semiconductor chip is connected to a ~~the~~ respective outer connection metallization by a wire bond connection, characterized in that the inner connection metallization comprises a reinforcing system having an open grid structure on the doped silicon substrate, wherein the open grid structure exposes the doped silicon substrate to direct contact with the inner connection metallization.

2. (original) A semiconductor component as claimed in claim 1, characterized in that the reinforcing system having an open grid structure is formed from an insulation coating.

3. (original) A semiconductor component as claimed in claim 1, characterized in that the grid structure is formed so as to be an open groove structure.

4. (original) A semiconductor component as claimed in claim 1, characterized in that the grid structure may be formed so as to be an open tube structure.

5. (original) A semiconductor component as claimed in claim 1, characterized in that the area of the grid structure of thermal oxide constitutes >50% of the area of the contact window.

6. (new) A semiconductor component as claimed in claim 1, wherein the open grid structure comprises grid lands and wherein a ratio of height, h, to width, b, of the grid

lands is in the range of 1:25 to 1:50.

7. (new) A semiconductor component as claimed in claim 1, wherein the open grid structure comprises grid lands and grid openings and wherein the ratio between the area of the grid lands and the area of the grid openings is greater than 70%.

8. (new) A semiconductor component as claimed in claim 1, wherein the open grid structure of the reinforcing system comprises oxide lands formed directly on the doped silicon substrate.

9. (new) A semiconductor component comprising a semiconductor chip made of a doped silicon substrate, which chip is doped into a semiconductor device and structured, and comprises an inner connection metallization in a contact window, and said inner connection metallization of said semiconductor chip is connected to the respective outer connection metallization by a wire bond connection, characterized in that the inner connection metallization comprises a reinforcing system having an open grid structure on the doped silicon substrate, wherein the open grid structure forms at least one opening within which the inner connection metallization is in direct contact with the doped silicon substrate.

10. (new) A semiconductor component as claimed in claim 9, characterized in that the reinforcing system having an open grid structure is formed from an insulation coating.

11. (new) A semiconductor component as claimed in claim 9, characterized in that the grid structure is formed so as to be an open groove structure.

12. (new) A semiconductor component as claimed in claim 9, characterized in that the grid structure may be formed so as to be an open tube structure.

13. (new) A semiconductor component as claimed in claim 9, characterized in that the

area of the grid structure of thermal oxide constitutes >50% of the area of the contact window.

14. (new) A semiconductor component comprising:

discrete semiconductor device comprising:

a silicon substrate having an emitter and a base;

the emitter having an emitter contact formed thereon, the emitter contact comprising an inner connection metallization and a reinforcing system having an open grid structure, wherein the open grid structure exposes the silicon substrate to direct contact with the inner connection metallization;

the base having a base contact formed thereon, the base contact comprising an inner connection metallization and a reinforcing system having an open grid structure, wherein the open grid structure exposes the silicon substrate to direct contact with the inner connection metallization;

a leadframe having connection pins; and

a bond wire connected between the emitter contact and a connection pin of the leadframe; and

a bond wire connected between the base contact and the a connection pin of the leadframe.

15. (new) A semiconductor component as claimed in claim 14, characterized in that the reinforcing system having an open grid structure is formed from an insulation coating.

16. (new) A semiconductor component as claimed in claim 14, characterized in that the grid structure is formed so as to be an open groove structure.

17. (new) A semiconductor component as claimed in claim 14, characterized in that the grid structure may be formed so as to be an open tube structure.

18. (new) A semiconductor component as claimed in claim 14, characterized in that the

area of the grid structure of thermal oxide constitutes >50% of the area of the contact window.

19. (new) A semiconductor component as claimed in claim 14, wherein the open grid structure of the reinforcing system comprises oxide lands formed directly on the silicon substrate.